Excellent Integrated System Limited

Stocking Distributor

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Vishay Semiconductor/Diodes Division
VS-5ECH06-M3/9AT

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Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite
Datasheet of VS-5ECH06-M3/9AT - DIODE GEN PURP 600V 5A DO214AB
Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

New Product

VS-5ECH06-M3

www.vishay.com

Vishay Semiconductors

Hyperfast Rectifier, 5 A FRED Pt®

SMC (DO-214AB)

FEATURES

- Hyperfast recovery time, reduced Q_{rr} and soft recovery
- 175 °C maximum operating junction temperature
- For PFC CRM/CCM, snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according to JEDEC-JESD47
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

PRODUCT SUMMARY	
Package	SMC
$I_{F(AV)}$	5 A
V_R	600 V
V_F at I_F	1.95 V
t_{rr} typ.	30 ns
T_J max.	175 °C
Diode variation	Single die

DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		600	V
Average rectified forward current	$I_{F(AV)}$	T_L = 73 °C (1)	5	
Non-repetitive peak surge current	I_{FSM}	T_J = 25 °C	90	A
Operating junction and storage temperatures	T_J, T_{Stg}		- 55 to 175	°C

Note

(1) Mounted on PCB with minimum pad size

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	I_R = 100 µA	600	-	-	V
Forward voltage	V_F	I_F = 5 A	-	1.65	1.95	
		I_F = 5 A, T_J = 150 °C	-	1.2	1.4	
Reverse leakage current	I_R	V_R = V_R rated	-	-	3	µA
		T_J = 150 °C, V_R = V_R rated	-	-	100	
Junction capacitance	C_T	V_R = 600 V	-	7.8	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time	t_{rr}	I_F = 1.0 A, dI_F/dt = 100 A/µs, V_R = 30 V		-	30	-	ns
		I_F = 1.0 A, dI_F/dt = 50 A/µs, V_R = 30 V		-	35	-	
		I_F = 0.5 A, I_R = 1 A, I_{rr} = 0.25 A		-	-	35	
		T_J = 25 °C	I_F = 5 A dI_F/dt = 200 A/µs V_R = 390 V	-	23	-	
		T_J = 125 °C		-	38	-	
Peak recovery current	I_{RRM}	T_J = 25 °C		-	3.5	-	A
		T_J = 125 °C		-	5.4	-	
Reverse recovery charge	Q_{rr}	T_J = 25 °C		-	41	-	nC
		T_J = 125 °C		-	111	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Maximum junction and storage temperature range	T_J, T_{Stg}		- 55	-	175	°C
Thermal resistance, junction to case	R_{thJC} (1)		-	-	14	°C/W
Thermal resistance, junction to ambient	R_{thJA} (1)		-	-	80	
Approximate Weight			0.24			g
			0.008			oz.
Marking device		Case style SMC (DO-214AB)	5H6			

Note

(1) Mounted on PCB with minimum pad size

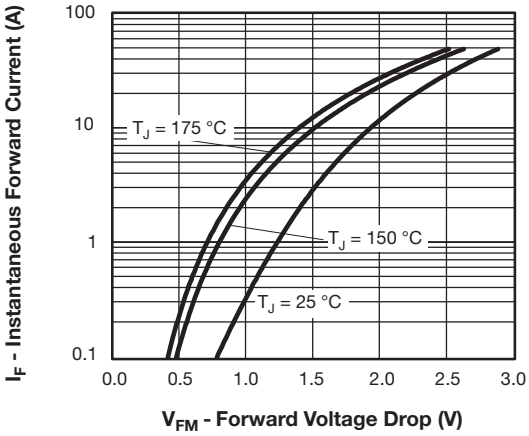

Fig. 1 - Typical Forward Voltage Drop Characteristics

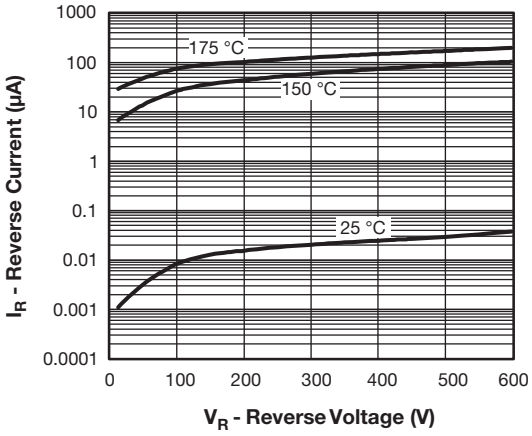

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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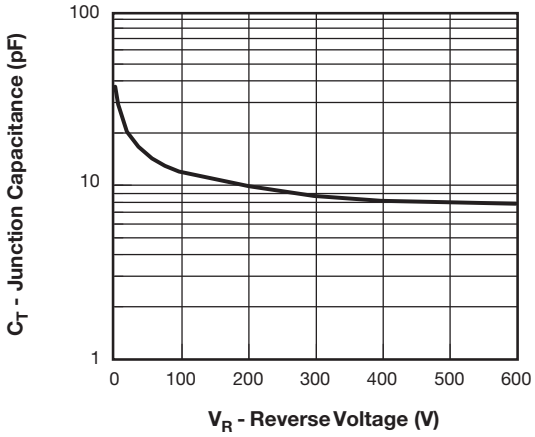

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

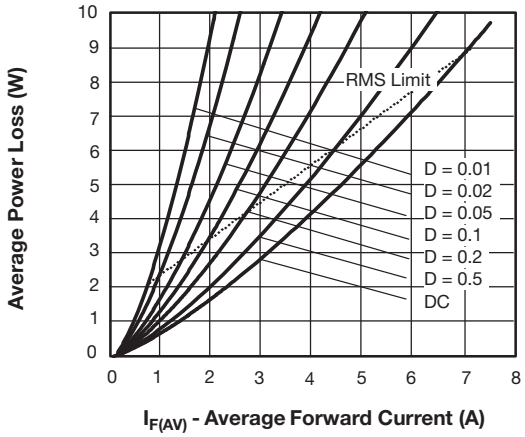

Fig. 5 - Forward Power Loss Characteristics

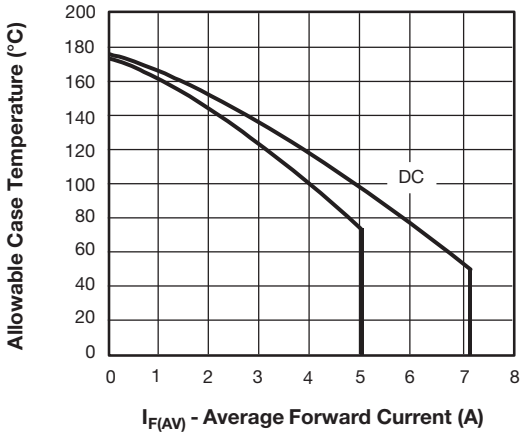

Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

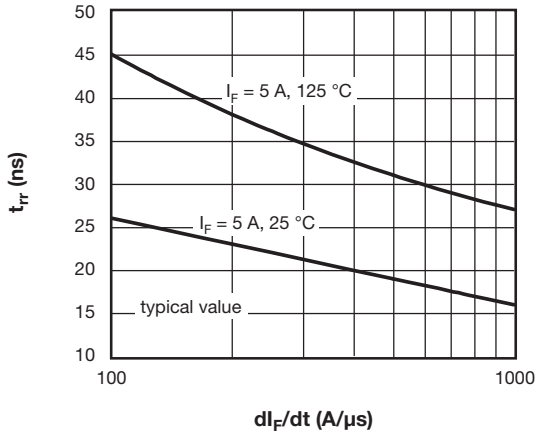

Fig. 6 - Typical Reverse Recovery vs. dI_F/dt

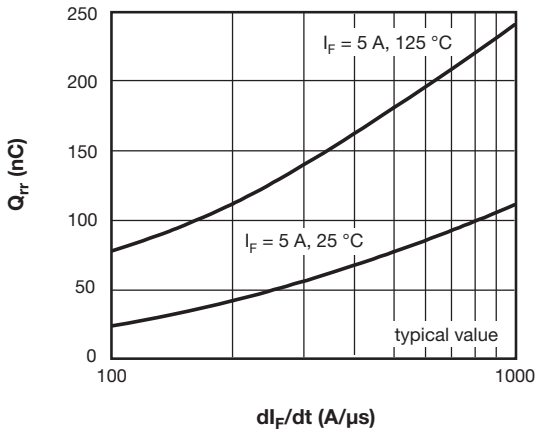

Fig. 7 - Typical Stored Charge vs. dI_F/dt

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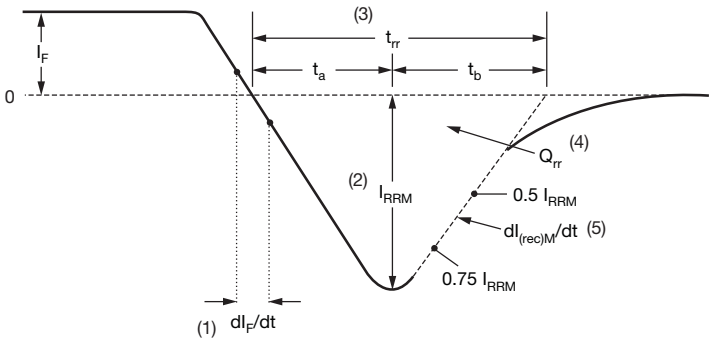

(1) dI_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code

VS-	5	E	C	H	06	-M3
1	2	3	4	5	6	7

1 - Vishay Semiconductors product

2 - Current rating (5 = 5 A)

3 - Circuit configuration:
E = Single diode

4 - C = SMC package

5 - Process type,
H = Hyperfast recovery

6 - Voltage code (06 = 600 V)

7 - M3 = Halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	**QUANTITY PER TUBE**	**MINIMUM ORDER QUANTITY**	**PACKAGING DESCRIPTION**
VS-5ECH06-M3/9AT	9AT	3500	13"diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95402
Part marking information	www.vishay.com/doc?95472
Packaging information	www.vishay.com/doc?95404

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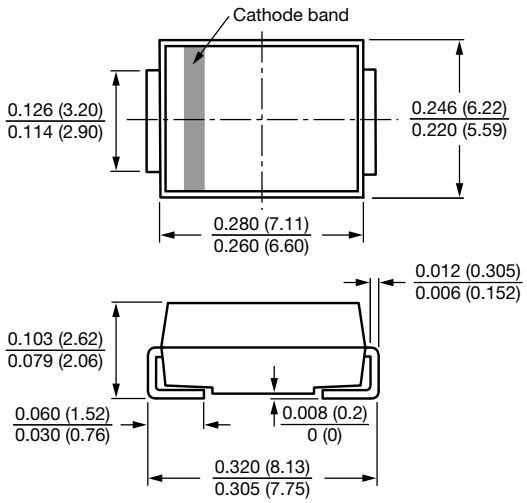
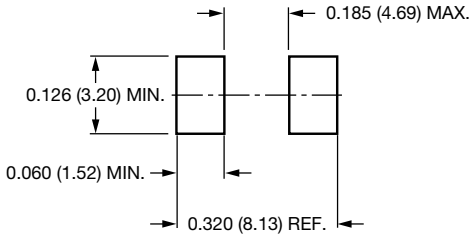
SMC

DIMENSIONS in inches (millimeters)

DO-214AB (SMC)



Mounting Pad Layout



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